

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor laser, comprising:

at least one absorbing layer ~~(8)~~ within the laser resonator, said absorbing layer configured to reduce ~~reducing~~ the transmission T_{Res} of the laser radiation ~~(10)~~ in the laser resonator and decrease ~~for the purpose of decreasing~~ the sensitivity of the semiconductor laser to disturbances created by the radiation ~~(9)~~ fed back into the laser resonator.

2. (Currently Amended) The semiconductor laser as claimed in claim 1, ~~in which~~ wherein the absorbing layer ~~(8)~~ is situated in a node of a standing wave that forms during operation of the semiconductor laser in the laser resonator.

3. (Currently Amended) The semiconductor laser as claimed in claim 1, ~~in which~~ wherein the reflectivity of the mirrors of the resonator and the transmission T_{Res} of the laser radiation during a resonator circulation are set ~~so as~~ to produce a low sensitivity to disturbances for a wide range of possible output powers of the semiconductor laser.

4. (Currently amended) The semiconductor laser as claimed in claim 1 ~~in which~~ wherein the semiconductor laser is a single-mode laser.

5. (Currently Amended) The semiconductor laser as claimed in claim 1, ~~in which~~

wherein the semiconductor laser is a surface emitting semiconductor laser (VCSEL).

6. (Currently Amended) The semiconductor laser as claimed in claim 1, ~~in which~~
wherein the semiconductor laser is a surface emitting semiconductor laser with an external resonator (VECSEL).

7. (Currently Amended) The semiconductor laser as claimed in claim 6, ~~in which~~
wherein the surface emitting semiconductor laser ~~contains~~ comprises a Bragg mirror (4) and the absorbing layer (8) is ~~contained~~ disposed in said Bragg mirror (4).

8. (Currently Amended) The semiconductor laser as claimed in claim 1, ~~in which~~
wherein the absorbing layer (8) is a gallium arsenide layer.

9. (Currently Amended) The semiconductor laser as claimed in claim 1, ~~in which~~
wherein the gallium arsenide layer is approximately 20 nm thick.

10. (Currently amended) The semiconductor laser as claimed in claim 1, ~~which contains~~
further comprising a plurality of absorbing layers within the laser resonator.

11. (Currently Amended) The semiconductor laser as claimed in claim 5, ~~in which~~
wherein the surface emitting semiconductor laser ~~contains~~ comprises a Bragg mirror (4) and the absorbing layer (8) is contained in said Bragg mirror (4).